



Micro Commercial Components  
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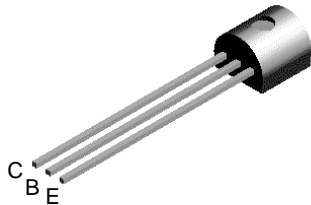
# S9015

## PNP Silicon Transistors

### Features

- TO-92 Plastic-Encapsulate Transistors
- Capable of 0.45Watts( $T_{amb}=25^{\circ}C$ ) of Power Dissipation.
- Collector-current 0.1A
- Collector-base Voltage 50V
- Operating and storage junction temperature range:  $-55^{\circ}C$  to  $+150^{\circ}C$
- Marking Code: S9015

Pin Configuration



Electrical Characteristics @  $25^{\circ}C$  Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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#### OFF CHARACTERISTICS

$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ( $I_C=100\mu A_{dc}$ , $I_E=0$ )	50	---	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ( $I_C=1.0mA_{dc}$ , $I_E=0$ )	45	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( $I_E=100\mu A_{dc}$ , $I_C=0$ )	5.0	---	Vdc
$I_{CBO}$	Collector Cutoff Current ( $V_{CB}=50V_{dc}$ , $I_E=0$ )	---	0.05	$\mu A_{dc}$
$I_{EBO}$	Emitter Cutoff Current ( $V_{EB}=5.0V_{dc}$ , $I_C=0$ )	---	0.05	$\mu A_{dc}$

#### ON CHARACTERISTICS

$h_{FE}$	DC Current Gain ( $I_C=1.0mA_{dc}$ , $V_{CE}=5.0V_{dc}$ )	60	1000	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ( $I_C=100mA_{dc}$ , $I_E=10mA_{dc}$ )	---	0.3	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ( $I_C=100mA_{dc}$ , $I_E=10mA_{dc}$ )	---	1.0	Vdc

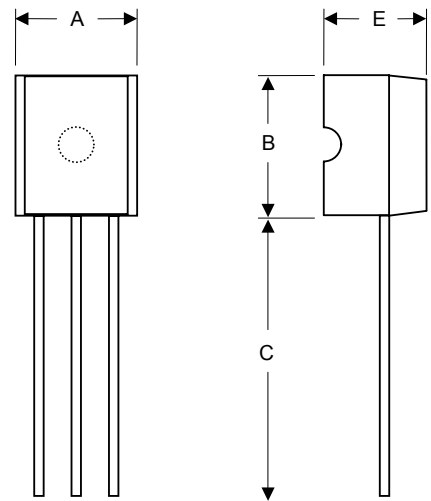
#### SMALL-SIGNAL CHARACTERISTICS

$f_T$	Transistor Frequency ( $I_C=10mA_{dc}$ , $V_{CE}=5.0V_{dc}$ , $f=30MHz$ )	150	---	MHz
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#### CLASSIFICATION OF $h_{FE(1)}$

Rank	A	B	C1	C2	C3	D
Range	60-150	120-200	200-300	300-400	400-500	500-1000

### TO-92



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	